SOP-8 MOS

Complementary Enhancement MOSFET in a SOP-8 Plastic Package.

N-channel	P-channel
V_{DS}(V)=60V	V_{DS}(V)=-60V
I_D=9.7A	I_D-3.4A
$R_{DS(ON)}$<16mΩ (V_{GS}=10V)	$R_{DS(ON)}$<100mΩ (V_{GS}=-10V)
$R_{DS(ON)}$<22mΩ (V_{GS}=4.5V)	$R_{DS(ON)}$<130mΩ (V_{GS}=-4.5V)

HF Product.

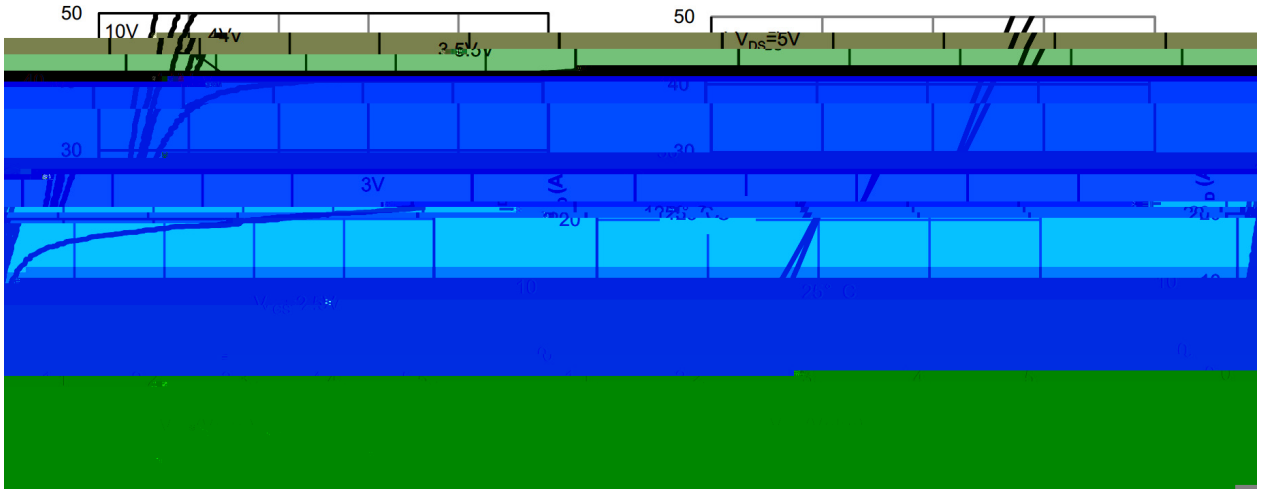
DC/DC

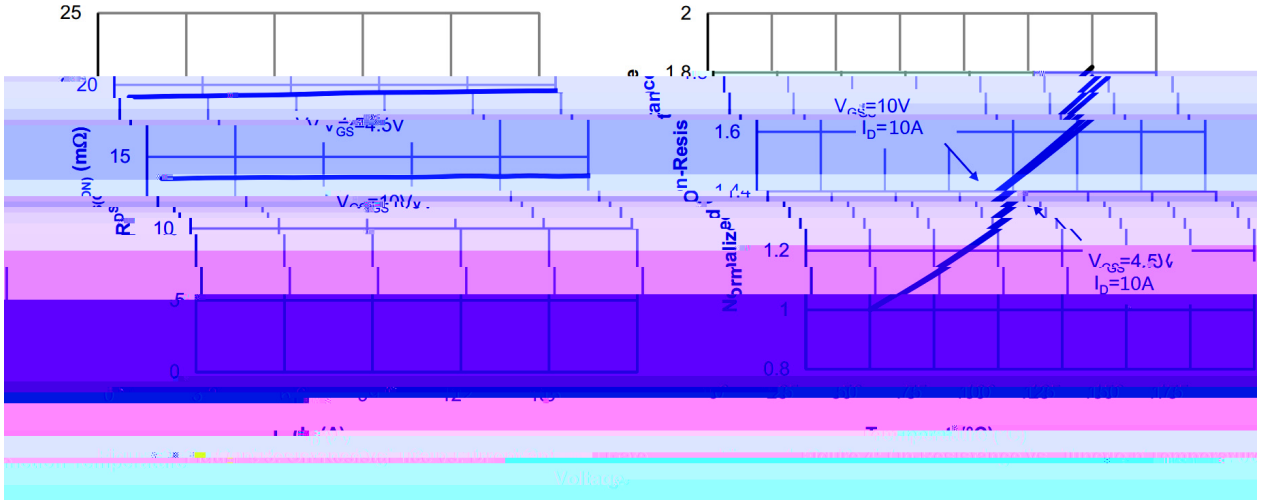
These devices are well suited for

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol		Rating		Unit
			N-channel	P-channel	
Drain-Source Voltage	V_{DSS}		60	-60	V
Gate-Source Voltage	V_{GSS}		±20		V
Continuous Drain Current	I_D (T_A=25)		9.7	-3.4	A
Pulsed Drain Current	I_{DM}		±40		A
Power Dissipation	P_D (T_A=25)		2.7	1.9	W
Maximum Junction-to-Ambient	$R_{\theta JA}$	tò10s	46.3	65.8	/W
		Steady-State	72	100	/W
Junction and Storage Temperature Range	T_J,T_{STG}		-55 to +150		

N- / N-CHANNEL Electrical Characteristic Curve





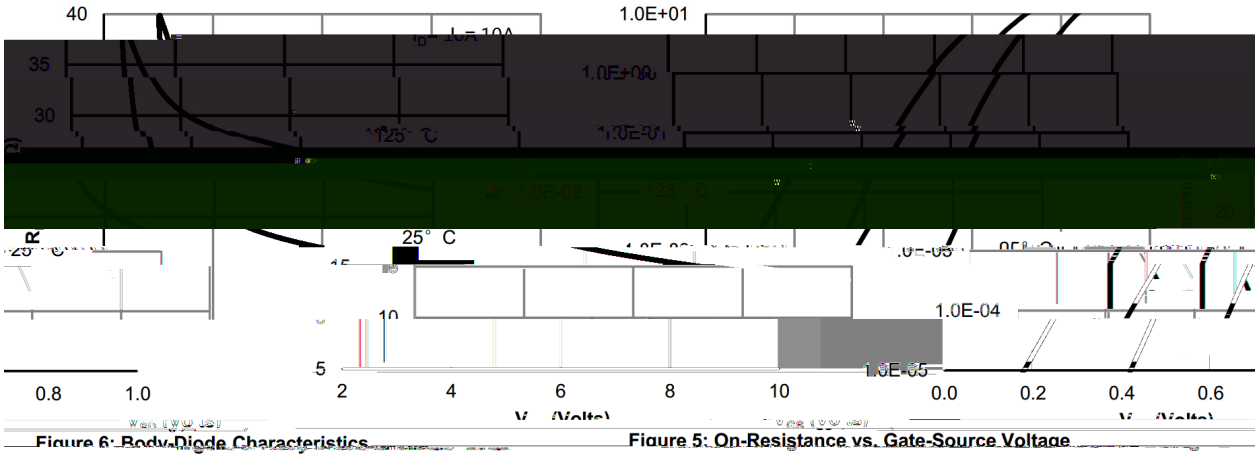
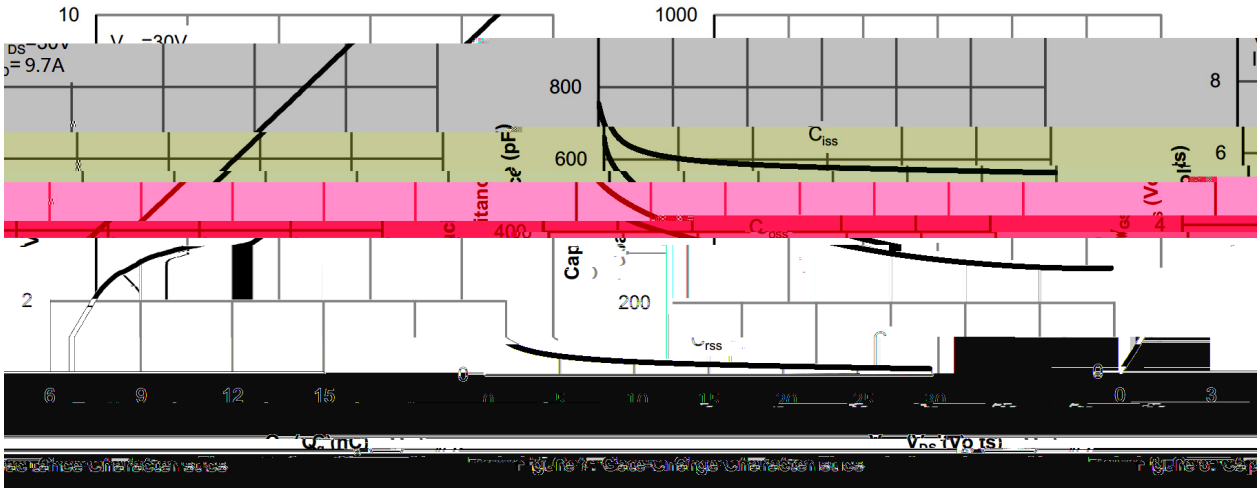
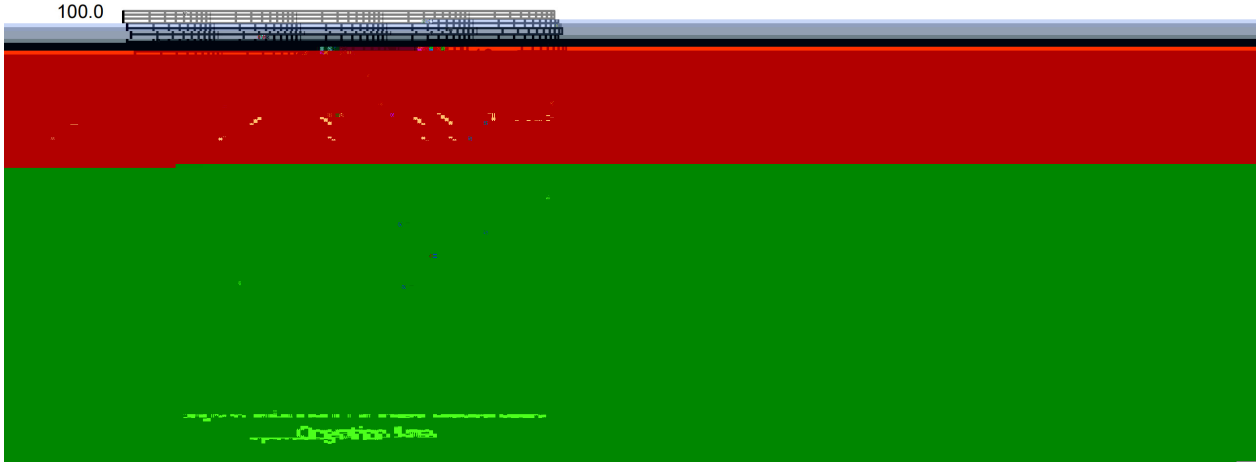


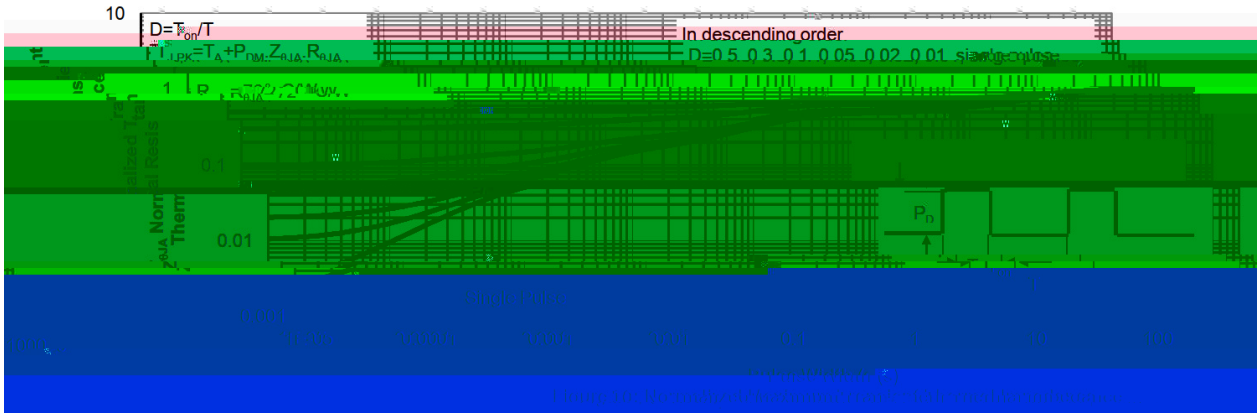
Figure 6: Body-Diode Characteristics

Figure 5: On-Resistance vs. Gate-Source Voltage

N- / N-CHANNEL Electrical Characteristic Curve







P- / P-CHANNEL Electrical Characteristic Curve

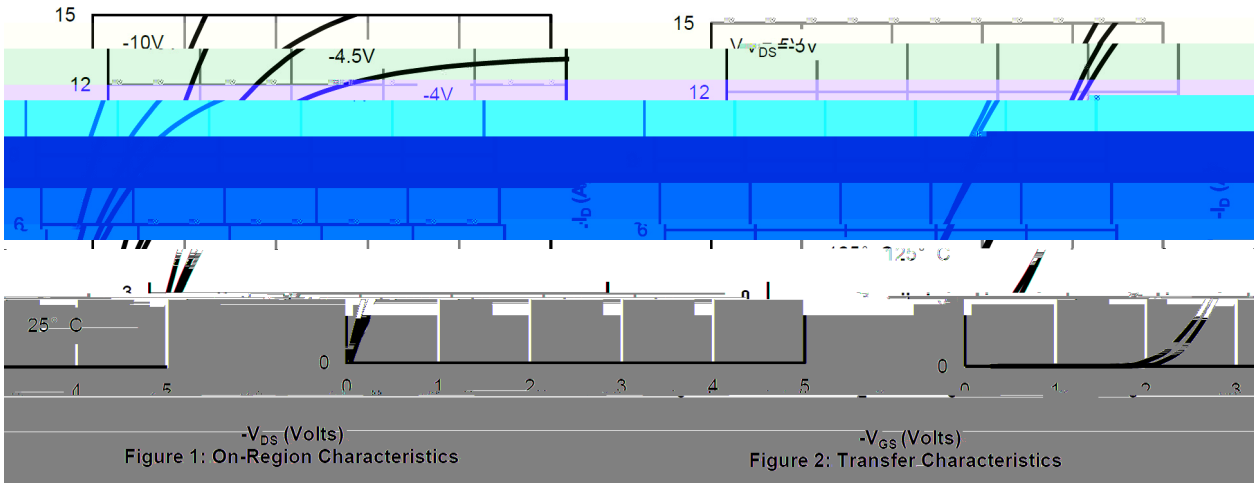
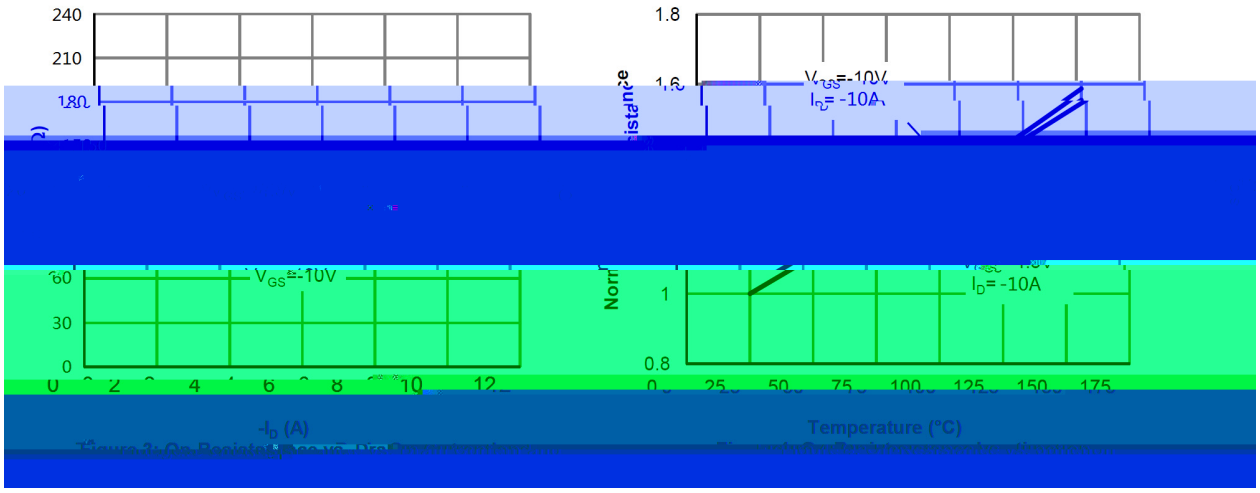


Figure 1: On-Region Characteristics

Figure 2: Transfer Characteristics



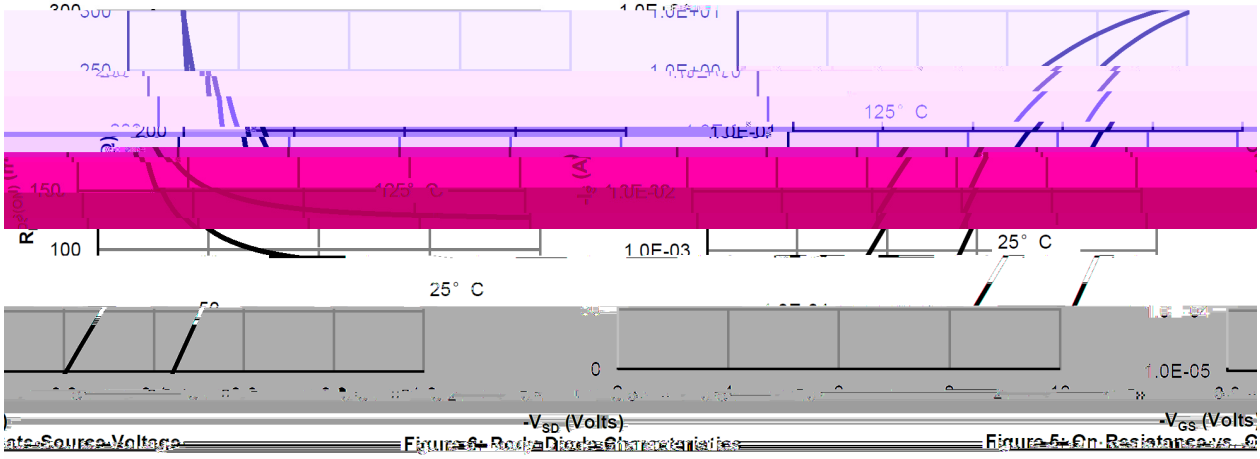
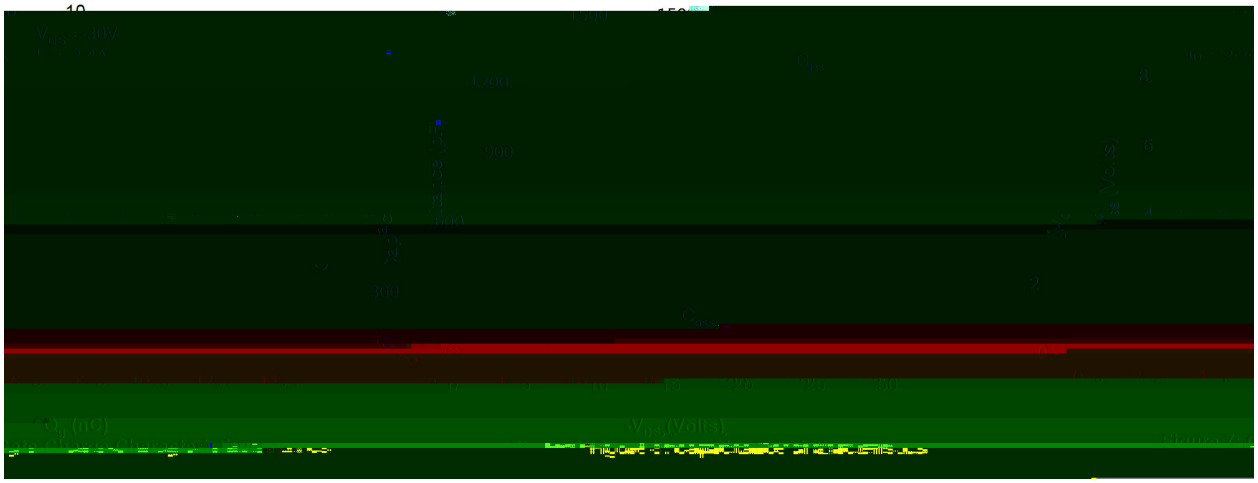
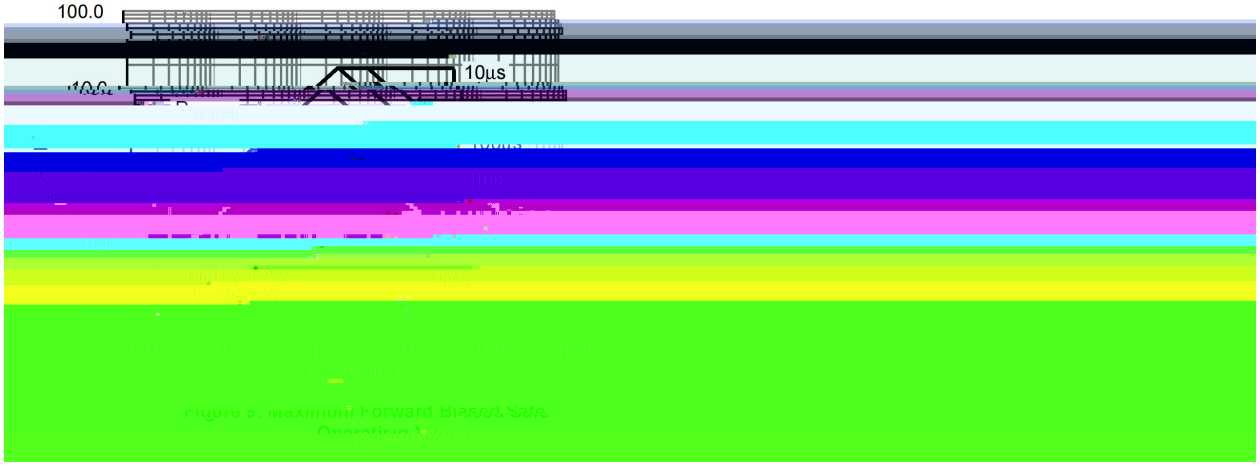
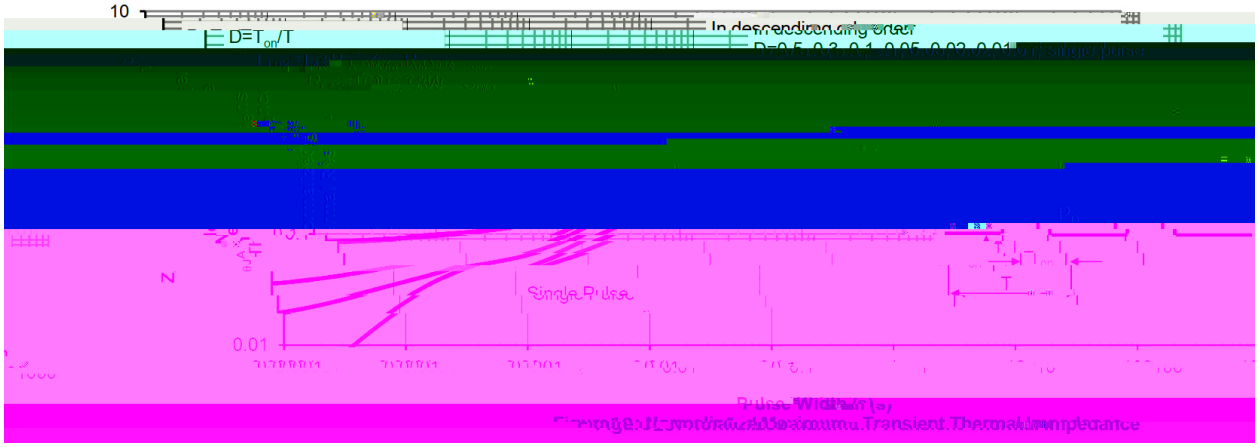


Figure 5: On-Resistance vs. G

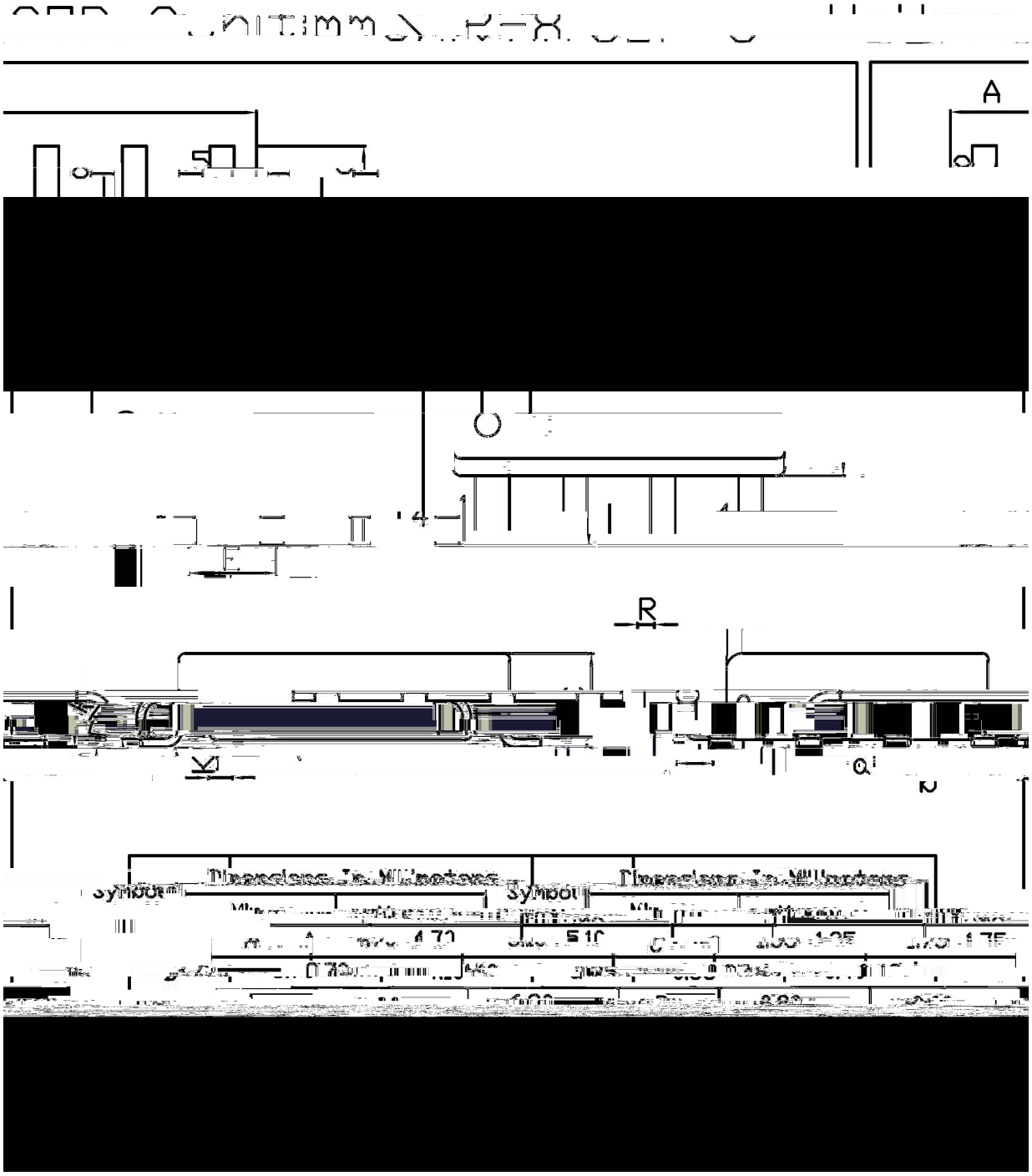
P- / P-CHANNEL Electrical Characteristic Curve



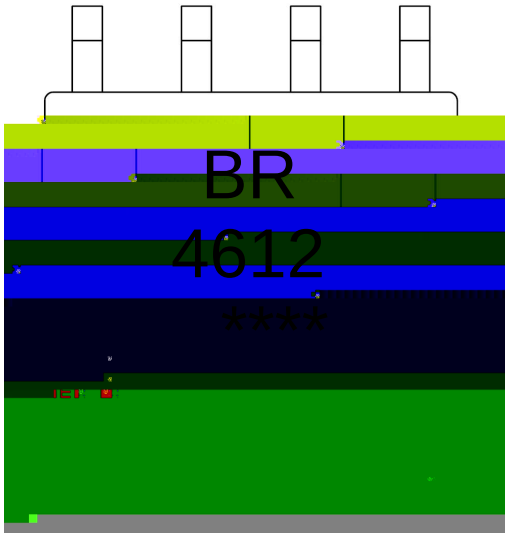




/ Package Dimensions



/ Marking Instructions



BR

4612

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Note:

BR:	Company Code
4612:	Product Type Code
****:	Lot No. Code, code change with Lot No

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

1	150	180	60	90sec;	1.Preheating:	10.5	127.3(1.Pr.Preheatin.)-1260	668.TD0		